



### 60V PNP LOW SATURATION TRANSISTOR IN U-DFN2020-3

### **Features**

- BVcEo > -60V
- hFE Specified up to- 5A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

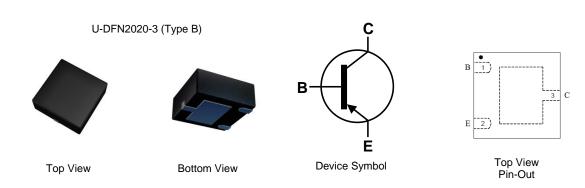
https://www.diodes.com/quality/product-definitions/

## **Mechanical Data**

- Case: U-DFN2020-3 (Type B)
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208
- Weight: 0.01 grams (Approximate)

## **Applications**

- DC-DC Converters
- Charging Circuits
- Motor Control
- Power Switches



## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP5860CFDB-7	2F0	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



2F0= Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

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	Year	2019		2020	2021		2022	2023	1	2024	2025		2026
	Code	G		Н			J	K		L	M		N
	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	Vcво	-60	
Collector-Emitter Voltage	VCEO	-60	V
Emitter-Base Voltage	VEBO	-7	
Peak Pulse Current	Ісм	-8	۸
Continuous Collector Current	Ic	-4	A

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Dawar Dissination	(Note 5)	0-	0.69	W	
Power Dissipation	(Note 6)	PD	1.25	VV	
Thermal Decistores, Junction to Ambient	(Note 5)	2	180		
Thermal Resistance, Junction to Ambient	(Note 6)	RθJA	100	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

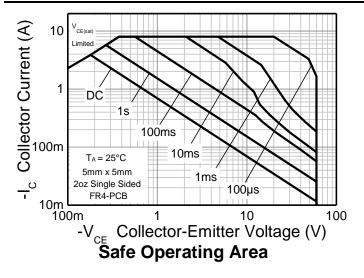
<sup>5.</sup> For a device mounted with the exposed collector on 5mm x 5mm 2oz copper on single sided FR4 PCB; device is measured under still air conditions whilst operating in the steady state.

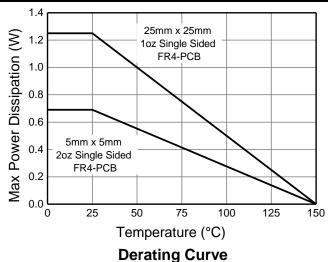
6. Same as Note (5) except the exposed collector pad is mounted on 25mm x 25mm 1oz copper.

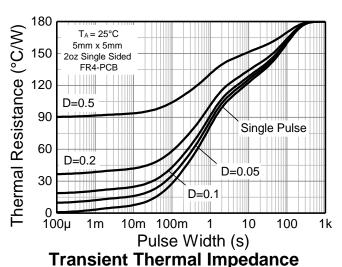
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

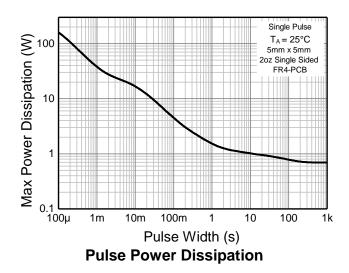


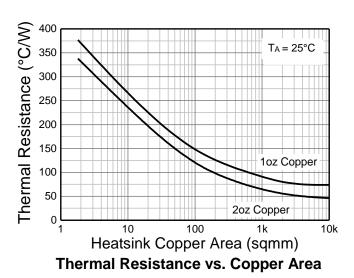
## **Thermal Characteristics and Derating Information**

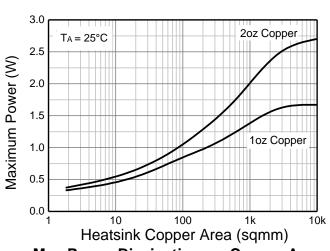












Max Power Dissipation vs. Copper Area



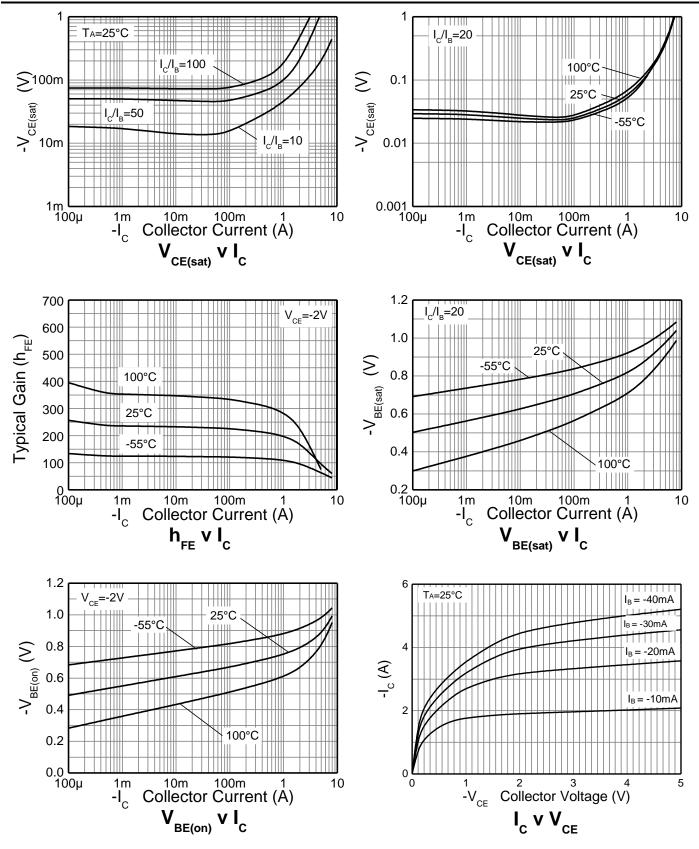
# Electrical Characteristics (@TA = +25°C, unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	-60	_	_	V	$I_{C} = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 8)	BVceo	-60	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	_		V	$I_E = -100 \mu A$
Collector Cutoff Current	Ісво	_	_	-100	nA	V <sub>CB</sub> = -48V
Emitter Cutoff Current	I <sub>EBO</sub>		_	-100	nA	V <sub>EB</sub> = -6V
Collector Emitter Cutoff Current	ICES	_	_	-100	nA	V <sub>CES</sub> = -48V
		170	220	_		Ic = -500mA, VcE = -2V
Static Forward Current Transfer Ratio (Note 8)	hFE	160	205	_		Ic = -1A, VcE = -2V
Static Forward Current Transfer Ratio (Note 8)	IIFE	140	180	_	_	Ic = -2A, VcE = -2V
		170	100	_		Ic = -5A, VcE = -2V
		_	-40	-55		$I_C = -0.5A$ , $I_B = -50mA$
	VCE(sat)	_	-65	-105	mV	Ic = -1A, I <sub>B</sub> = -50mA
Collector-Emitter Saturation Voltage (Note 8)		_	-175	-230		Ic = -1A, I <sub>B</sub> = -10mA
		_	-155	-300		$I_C = -4A$ , $I_B = -400mA$
		_	-355	-450		I <sub>C</sub> = -5A, I <sub>B</sub> = -250mA
Base-Emitter Turn-On Voltage (Note 8)	V <sub>BE(on)</sub>	_	-0.75	-0.9	V	Ic = -2A, VcE = -2V
Base-Emitter Saturation Voltage (Note 8)	\/	_	-0.75	-0.9	V	Ic = -1A, I <sub>B</sub> = -10mA
base-Emilier Saturation Voltage (Note 6)	VBE(sat)	-7 — — — — — — — — — — — — — — — — — — —	-0.95	-1.1	V	Ic = -5A, I <sub>B</sub> = -250mA
Output Capacitance	Cobo	_	65	80	pF	V <sub>CB</sub> = -10V, f = 1MHz
Transition Frequency	fτ	_	130	_	MHz	VcE = -10V, Ic = -100mA, f = 100MHz
Delay Time	t <sub>d</sub>	_	26	_		
Rise Time	tr	_	54	_	ne	
Turn-On Time	ton	_	80	_		Vcc = -9V, Ic = -2A
Storage Time	ts		205		ns	$I_{B1} = -I_{B2} = -0.1A$
Fall Time	tf	_	35	_		
Turn-Off Time	t <sub>off</sub>		240	_		

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

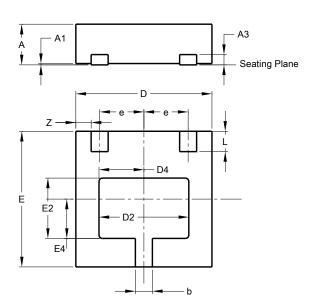




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## U-DFN2020-3 (Type B)

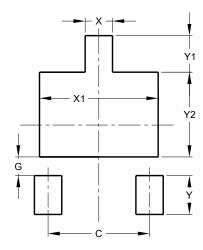


U-DFN2020-3 (Type B)							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.02				
А3	_	_	0.152				
b	0.20	0.30	0.25				
D	1.950	2.075	2.00				
D2	1.22	1.42	1.32				
D4	0.56	0.76	0.66				
Е	1.950	2.075	2.00				
E2	0.79	0.99	0.89				
E4	0.48	0.68	0.58				
е		-	0.65				
L	0.25	0.35	0.30				
Z	_	_	0.225				
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## U-DFN2020-3 (Type B)



Dimensions	Value (in mm)
С	1.300
G	0.240
Х	0.350
X1	1.520
Υ	0.500
Y1	0.470
Y2	1.090



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